

Amendments to the Specification.

Please amend the paragraph beginning at column 2, line 48 to read as follows:

An additional advantage of the present invention is that [is] it may provide higher productivity as compared to known processes.

Please amend the paragraph beginning at column 5, line 38 to read as follows:

Next, a conductive barrier 11 may be provided over the insulating layer. Preferably, the conductive barrier may include a layer of tantalum nitride first sputter deposited over the insulating layer, the walls of the recess, and the exposed conductive feature to a thickness of about 15 Å to about 500 Å and more typically to a thickness of about 50 to about 300 to act as adhesion promoting layer between the insulating layer and subsequently to be applied tantalum layer. Then, a tantalum layer may be sputtered over the layer of tantalum nitride, where it may form α -Ta spontaneously. Typically, the thickness of the tantalum layer is about 500 Å to about 3000 Å and more typically about 1000 Å to about 2000 Å. Also, α -Ta may be deposited directly over the insulator by sputtering methods. Typically, the thickness of the α -Ta is about 500 Å to about 5000 Å, and more typically about 1000 Å to about 3000.

Please amend the paragraph beginning at column 6, line 3 to read as follows:

After formation of the seed layer, a photoresist may be deposited over the seed layer. Any of the well known photosensitive resist materials known in the art can be employed. The resist is typically applied by spinning on or by spraying.

Please amend the paragraph beginning at column 6, line 23 to read as follows:

The photoresist may be selectively removed everywhere except for the in [the] recess(es). The resist remaining in the recess(es) may [protects] protect the seed layer in the recesses (both the side walls and bottom of the recesses). The seed layer lying outside of the recesses may be removed simultaneously with the photoresist. Actually, since the seed layer lies under the photoresist, the seed layer may be removed subsequent to the removal of the photoresist. They may be removed by the same process.

Please amend the paragraph bridging columns 6 and 7 to read as follows:

The electroplating is continued until a desired amount of the conductive metal is plated in the recess(es). This usually takes about 10 min. to about 90 min, more typically about 20 min. to about 75 min. The thickness of the electroplated metal or alloy is typically about 25μ to about 200μ, and more typically about 40μ to about 75μ.

Please amend the paragraph bridging columns 5 and 6 to read as follows:

After the deposition of the barrier layer, a seed layer 13 may be deposited over the barrier layer 11 including on the walls and bottom of the recess(es). The preferred seed

layer is copper, which can be deposited by sputtering or evaporation and preferably by sputtering. The copper may be sputtered employing temperatures of less than about 150.degree. C, preferably less than about 100°C, such as about 100°C to about -10°C. The sputtering may be carried out in the absence of an anneal. The sputtering is typically carried out to provide a seed layer of about 100 Å to about 2000 Å and preferably about 400 Å to about 1000 Å. Also, the copper seed layer may be deposited by CVD methods or by electroless plating method or by an electrolytic plating method.